# **N-Channel JFET**

-25 V, 20 to 40 mA, 40 mS, Dual

# NSVJ6904DSB6

The NSVJ6904DSB6 is a composite type of JFET designed for compact size and high efficiency which can achieve high gain performance. This AEC-Q101 qualified and PPAP capable device is suited for automotive applications.

#### **Features**

- Large | yfs |
- Small Ciss
- Ultralow Noise Figure
- CPH6 Package is Pin-Compatible with SC-74
- AEC-Q101 Qualified and PPAP Capable
- Mounting Area is Greatly Reduced by Incorporating Two JFETs of the NSVJ3910SB3 in One Package of CPH6 Compared with Using Two Separate Packages

# **Typical Applications**

- AM Tuner RF Amplification
- Low Noise Amplifier

#### **Specifications**

# ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbo I	Value	Unit
Drain to Source Voltage	$V_{DSX}$	25	V
Gate to Drain Voltage	$V_{GDS}$	-25	V
Gate Current	I <sub>G</sub>	10	mA
Drain Current	I <sub>D</sub>	50	mA
Allowable Power Dissipation 1 unit	$P_{D}$	400	mW
Total Power Dissipation	P <sub>T</sub>	700	mW
Operating Junction and Storage Temperature	T <sub>J,</sub> T <sub>Stg</sub>	-55 to +150	°C
	<b>-</b>		

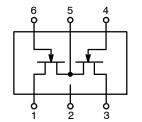
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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# ELECTRICAL CONNECTION N-Channel



- 1 : Drain 1 2 : NC
- 3 : Drain 2 4 : Gate 2
- 5: Source 1 / Source 2
- 6 : Gate 1

MARKING DIAGRAM





CASE 318BD

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

# NSVJ6904DSB6

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C, (Note 1))

Characteristic	Symbol	Conditions	Min	Тур	Max	Unit
Gate to Drain Breakdown Voltage	V <sub>(BR)GDS</sub>	$I_G = -10 \mu A, V_{DS} = 0 V$	-25	-	-	V
Gate to Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = -10 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	-1.0	nA
Cutoff Voltage	V <sub>GS(off)</sub>	$V_{DS} = 5 \text{ V}, I_D = 100 \mu\text{A}$	-0.6	-1.2	-1.8	V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 0 V	20	-	40	mA
Forward Transfer Admittance	yfs	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	30	40	-	mS
Input Capacitance	Ciss	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	6.0	-	pF
Reverse Transfer Capacitance	Crss		-	2.3	-	pF
Noise Figure	NF	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 0 V, f = 100 MHz	-	2.1	2.8	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>1.</sup> The specifications shown above are for each individual JFET.

# NSVJ6904DSB6

#### **CHARACTERISTICS**

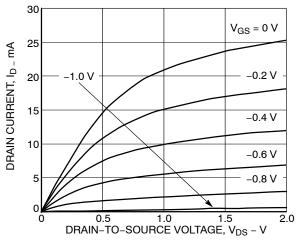


Figure 1. I<sub>D</sub> - V<sub>DS</sub>

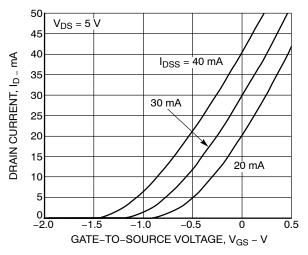


Figure 3. I<sub>D</sub> - V<sub>GS</sub>

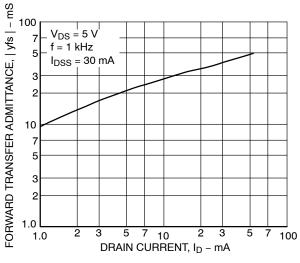


Figure 5. | yfs | - I<sub>D</sub>

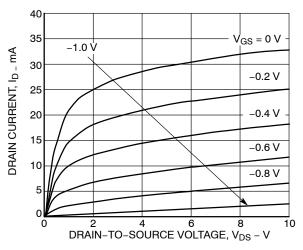


Figure 2.  $I_D - V_{DS}$ 

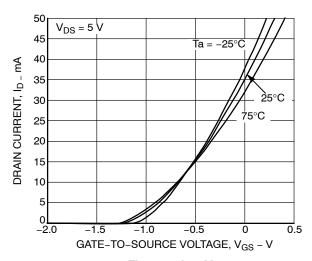


Figure 4. I<sub>D</sub> - V<sub>GS</sub>

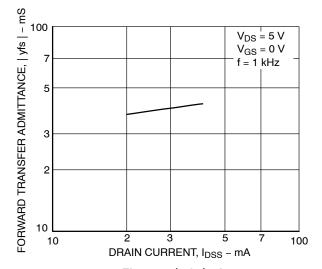


Figure 6. | yfs | - I<sub>DSS</sub>

## NSVJ6904DSB6

#### **CHARACTERISTICS**

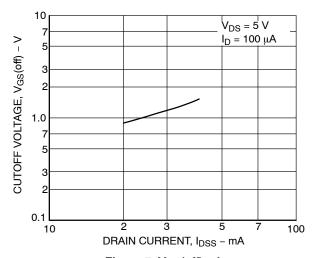


Figure 7. V<sub>GS</sub>(off) - I<sub>DSS</sub>

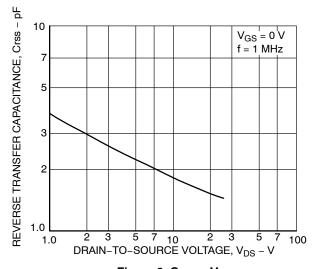


Figure 9. Crss - V<sub>DS</sub>

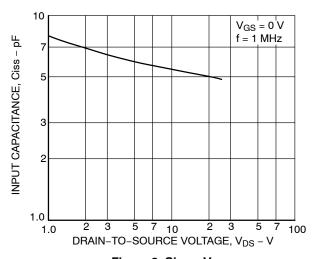


Figure 8. Ciss - V<sub>GDS</sub>

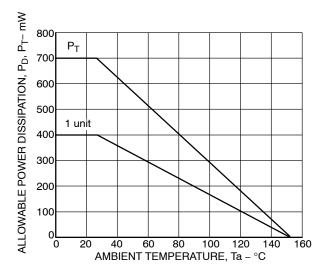


Figure 10.  $P_D$ ,  $P_T$  – Ta

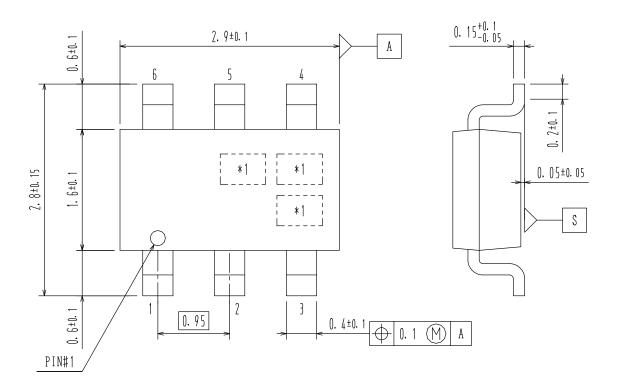
#### **ORDERING INFORMATION**

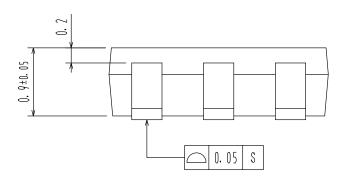
Device Order Number	Specific Device Marking	Package Type	Shipping <sup>†</sup>
NSVJ6904DSB6T1G	1P	CPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

CPH6 CASE 318BD ISSUE O

**DATE 30 NOV 2011** 





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